# **Silicon Power Transistors**

The MJL21193 and MJL21194 utilize Perforated Emitter technology and are specifically designed for high power audio output, disk head positioners and linear applications.

#### **Features**

- Total Harmonic Distortion Characterized
- High DC Current Gain
- Excellent Gain Linearity
- High SOA
- These Devices are Pb-Free and are RoHS Compliant\*

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	$V_{CEO}$	250	Vdc
Collector-Base Voltage	V <sub>CBO</sub>	400	Vdc
Emitter-Base Voltage	V <sub>EBO</sub>	5	Vdc
Collector-Emitter Voltage - 1.5 V	V <sub>CEX</sub>	400	Vdc
Collector Current - Continuous	Ic	16	Adc
Collector Current - Peak (Note 1)	I <sub>CM</sub>	30	Adc
Base Current - Continuous	I <sub>B</sub>	5	Adc
Total Power Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	P <sub>D</sub>	200 1.43	W W/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-65 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤2%

#### THERMAL CHARACTERISTICS

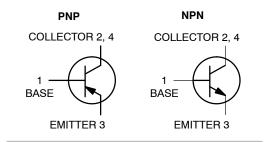
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.7	°C/W



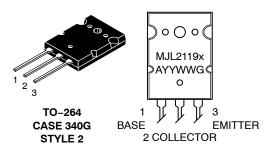
#### ON Semiconductor®

http://onsemi.com

# 16 AMPERE COMPLEMENTARY SILICON POWER TRANSISTORS 250 VOLTS, 200 WATTS



#### **MARKING DIAGRAM**



x = 3 or 4

A = Assembly Location

YY = Year
WW = Work Week
G = Pb-Free Package

#### ORDERING INFORMATION

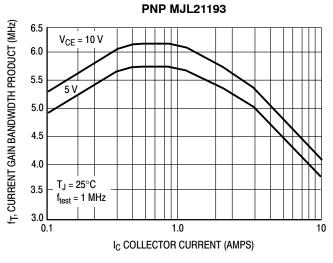
Device	Package	Shipping <sup>†</sup>
MJL21193G	TO-264 (Pb-Free)	25 Units / Rail
MJL21194G	TO-264 (Pb-Free)	25 Units / Rail

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### ELECTRICAL CHARACTERISTICS (T<sub>C</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit	
OFF CHARACTERISTICS		•		•	•	•
Collector-Emitter Sustaining Voltage (I <sub>C</sub> = 100 mAdc, I <sub>B</sub> = 0)	V <sub>CEO(sus)</sub>	250	-	-	Vdc	
Collector Cutoff Current (V <sub>CE</sub> = 200 Vdc, I <sub>B</sub> = 0)	I <sub>CEO</sub>	-	-	100	μAdc	
Emitter Cutoff Current (V <sub>CE</sub> = 5 Vdc, I <sub>C</sub> = 0)	I <sub>EBO</sub>	-	-	100	μAdc	
Collector Cutoff Current (V <sub>CE</sub> = 250 Vdc, V <sub>BE(off)</sub> = 1.5 Vdc)	I <sub>CEX</sub>	-	-	100	μAdc	
SECOND BREAKDOWN		•		•	•	-
Second Breakdown Collector Current with Base Forward (V <sub>CE</sub> = 50 Vdc, t = 1 s (non-repetitive) (V <sub>CE</sub> = 80 Vdc, t = 1 s (non-repetitive)	I <sub>S/b</sub>	4.0 2.25	_ _	_ _	Adc	
ON CHARACTERISTICS		•		•	•	
DC Current Gain ( $I_C = 8$ Adc, $V_{CE} = 5$ Vdc) ( $I_C = 16$ Adc, $I_B = 5$ Adc)		h <sub>FE</sub>	25 8	_ _	75 -	
Base-Emitter On Voltage (I <sub>C</sub> = 8 Adc, V <sub>CE</sub> = 5 Vdc)	V <sub>BE(on)</sub>	-	-	2.2	Vdc	
Collector–Emitter Saturation Voltage ( $I_C = 8$ Adc, $I_B = 0.8$ Adc) ( $I_C = 16$ Adc, $I_B = 3.2$ Adc)	V <sub>CE(sat)</sub>	_ _	- -	1.4 4	Vdc	
DYNAMIC CHARACTERISTICS						
1	FE	T <sub>HD</sub>		0.0		%
(Matched pair h <sub>FE</sub> = 50 @ 5 A/5 V) h <sub>I</sub>	nmatched FE atched		_	0.8	_	
Current Gain Bandwidth Product (I <sub>C</sub> = 1 Adc, V <sub>CE</sub> = 10 Vdc, f <sub>test</sub> = 1 MHz)	f⊤	4	-	-	MHz	
Output Capacitance (V <sub>CB</sub> = 10 Vdc, I <sub>E</sub> = 0, f <sub>test</sub> = 1 MHz)	C <sub>ob</sub>	-	-	500	pF	



NPN MJL21194  $f_{\mathrm{T}}$ , CURRENT GAIN BANDWIDTH PRODUCT (MHz) 8.0 7.0 10 V 6.0 5.0  $V_{CE} = 5 V$ 4.0 3.0 2.0  $T_J = 25^{\circ}C$ 1.0 f<sub>test</sub> = 1 MHz 0.1 1.0 10 I<sub>C</sub> COLLECTOR CURRENT (AMPS)

Figure 1. Typical Current Gain Bandwidth Product

Figure 2. Typical Current Gain Bandwidth Product

#### **TYPICAL CHARACTERISTICS**

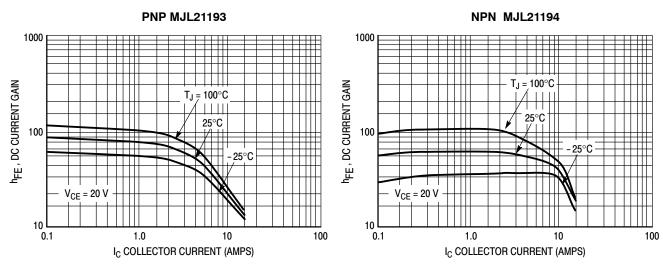


Figure 3. DC Current Gain, V<sub>CE</sub> = 20 V

Figure 4. DC Current Gain, V<sub>CE</sub> = 20 V

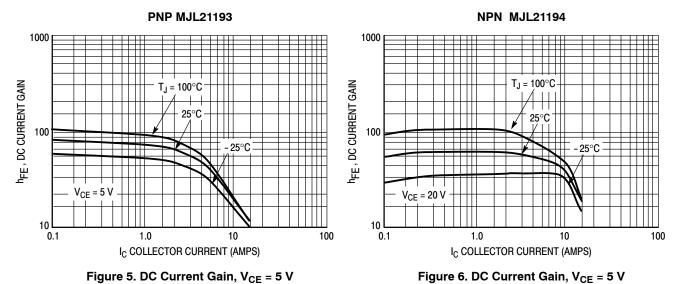


Figure 5. DC Current Gain, V<sub>CE</sub> = 5 V

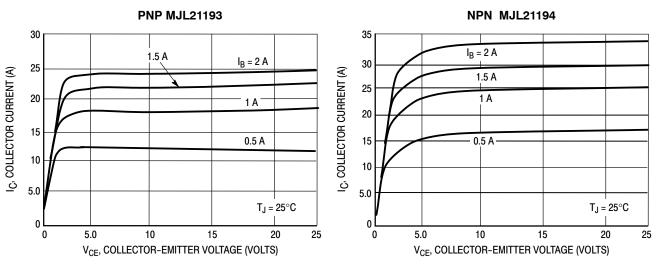


Figure 7. Typical Output Characteristics

Figure 8. Typical Output Characteristics

#### TYPICAL CHARACTERISTICS

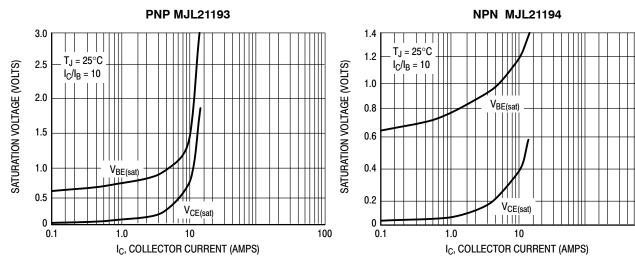


Figure 9. Typical Saturation Voltages

Figure 10. Typical Saturation Voltages

100

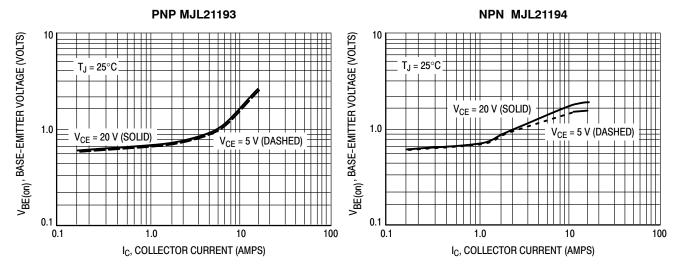


Figure 11. Typical Base-Emitter Voltage

Figure 12. Typical Base-Emitter Voltage

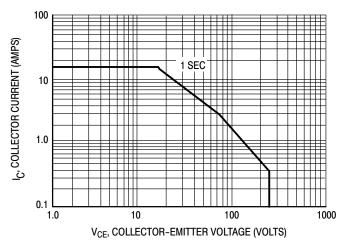


Figure 13. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor; average junction temperature and secondary breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 13 is based on  $T_{J(pk)} = 150^{\circ} C$ ;  $T_{C}$  is variable depending on conditions. At high case temperatures, thermal limitations will reduce the power than can be handled to values less than the limitations imposed by second breakdown.

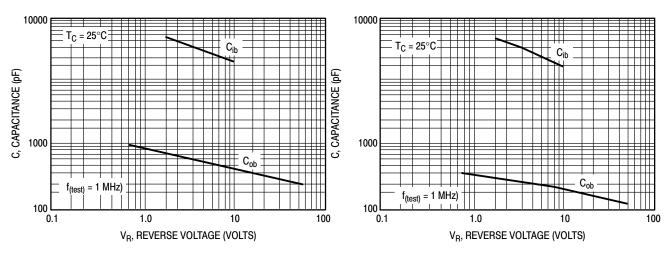


Figure 14. MJL21193 Typical Capacitance

Figure 15. MJL21194 Typical Capacitance

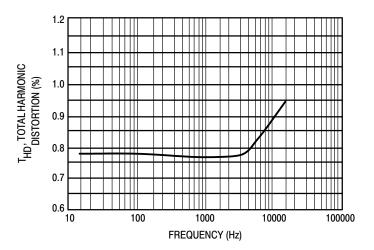


Figure 16. Typical Total Harmonic Distortion

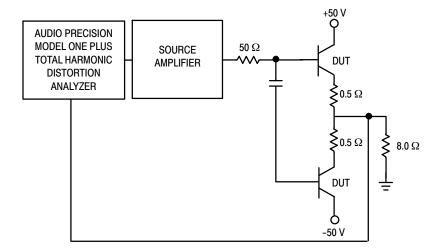
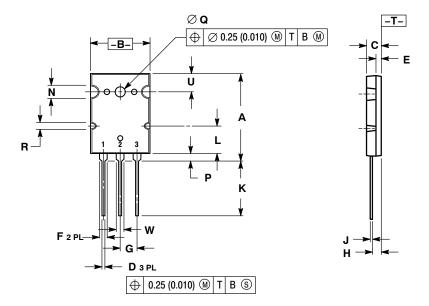


Figure 17. Total Harmonic Distortion Test Circuit

#### PACKAGE DIMENSIONS

TO-3BPL (TO-264) CASE 340G-02 **ISSUE J** 



#### NOTES

- DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: MILLIMETER.

	MILLIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	28.0	29.0	1.102	1.142	
В	19.3	20.3	0.760	0.800	
С	4.7	5.3	0.185	0.209	
D	0.93	1.48	0.037	0.058	
E	1.9	2.1	0.075	0.083	
F	2.2	2.4	0.087	0.102	
G	5.45	5.45 BSC		BSC	
Н	2.6	3.0	0.102	0.118	
J	0.43	0.78	0.017	0.031	
K	17.6	18.8	0.693	0.740	
L	11.2 REF		0.411 REF		
N	4.35 REF		0.172 REF		
P	2.2	2.6	0.087	0.102	
Q	3.1	3.5	0.122	0.137	
R	2.25 REF		0.089 REF		
U	6.3 REF		0.248 REF		
W	2.8	3.2	0.110	0.125	

STYLE 2: BASE PIN 1.

COLLECTOR

**EMITTER** 

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